

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
1	BRS	L1	219	rhodes near howard.in.	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/11/01 16:45	
2	BRS	L2	16	1 and (well near region)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/11/01 16:46	
3	BRS	L3	4	patrick near inna.in.	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/11/01 16:46	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
4	BRS	L4	0	mautitzson near richard.in.	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/11/0 1 16:47	
5	BRS	L5	56	438/84.ccls.	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/11/0 1 16:48	
6	BRS	L6	2976	(implant\$3) near15 (well near region)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/11/0 1 16:48	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
7	BRS	L7	428	(implant\$3) near15 (well near region) near25 (transistor)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/11/01 16:49	
8	BRS	L8	47	(implant\$3) near15 (well near region) near15 (conductivity) near25 (transistor)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/11/01 17:23	
9	BRS	L9	156	(implant\$3) near15 (well) near15 (conductivity) near25 (transistor or gate) near25 (substrate)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/11/01 17:24	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
10	BRS	L10	71	(implant\$3) near15 (well) near15 (second near conductivity) near25 (transistor or gate) near25 (substrate)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/11/0 1 17:44	
11	BRS	L11	19124	(implant\$3) near15 (well) near15 (second near conductivity) near25 (transistor or gate) (first near conductivity) near25 (substrate)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/11/0 1 17:44	
12	BRS	L12	59	(implant\$3) near15 (well) near15 (second near conductivity) near25 (transistor or gate) near15 (first near conductivity) near25 (substrate)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/11/0 1 17:57	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
13	BRS	L13	804	(well) near15 (second near conductivity) near25 (transistor or gate) near15 (first near conductivity) near25 (substrate)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/11/01 17:57	
14	BRS	L14	102	(implant\$3) near15 (well) near15 (first near conductivity) near25 (transistor or gate) near15 (first near conductivity) near25 (substrate)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/11/01 19:39	
15	BRS	L15	7	(implant\$3) near15 (well) near15 (first near conductivity) near25 (transistor or gate) near15 (first near conductivity) near25 (substrate) near25 (doped)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/11/01 17:58	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
16	BRS	L16	6	(implant\$3) near15 (well) near15 (dose) near25 (transistor or gate) near15 (first near conductivity) near25 (substrate)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/11/0 1 19:25	
17	BRS	L17	60	(implant\$3) near15 (well) near15 (dose) near25 (transistor or gate) near25 (substrate)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/11/0 1 19:26	
18	BRS	L18	24	(implant\$3) near15 (doped near region) near15 (dose) near25 (transistor or gate) near25 (substrate)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/11/0 1 19:26	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
19	BRS	L19	2	(ccd near imager) near15 (electrical near device)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/11/0 1 19:43	
20	BRS	L20	3	(implant\$3 near dose) near15 (doped near region) near15 (below)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/11/0 1 19:44	
21	BRS	L21	93	(implant\$3 near dose) near15 (doped near region)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/11/0 1 19:46	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
22	BRS	L22	78	(implant\$3 near dose) near15 (doped near region) near15 (dose)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/11/0 1 19:48	
23	BRS	L23	6	(implant\$3 near dose) near15 (doped near region) near15 (p-type)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/11/0 1 19:49	
24	BRS	L24	132	(implant\$3) near15 (doped near region) near15 (p-type) near5 (substrate)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/11/0 1 19:49	



	U	1	Document ID	Title	Current OR	Pages
1	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 20030001175 A1	Semiconductor device and method for fabricating the same	257/288	47
2	<input type="checkbox"/>	<input type="checkbox"/>	US 6627490 B2	Semiconductor device and method for fabricating the same	438/200	45
3	<input type="checkbox"/>	<input type="checkbox"/>	US 6472714 B1	Semiconductor device in which memory cells and peripheral circuits are provided on the same circuit	257/371	46
4	<input type="checkbox"/>	<input type="checkbox"/>	US 6429066 B1	Method for producing a polysilicon circuit element	438/239	40
5	<input type="checkbox"/>	<input type="checkbox"/>	US 5981324 A	Methods of forming integrated circuits having memory cell arrays and peripheral circuits therein	438/210	11

	U	1	Document ID	Title	Current OR	Pages
6	<input type="checkbox"/>	<input type="checkbox"/>	US 5893740 A	Method of forming a short channel field effect transistor	438/289	7